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a first doped zone of the first conductivity type coupled to the channel of said first MOS transistor; and

a current limiter coupled between the gate of said first MOS transistor and said first doped zone, said current limiter comprising a second doped zone of a second conductivity type in ohmic contact with said first doped zone.

2. (Once Amended) The device according to claim 1, wherein the current limiter comprises a second transistor, the second doped zone embodying the source of said second transistor.

3. (Once Amended) The device according to claim 2, wherein the second transistor includes a gate coupled to a gate polarization terminal.

4. (Once Amended) The device according to claim 2, wherein the second transistor has a gate coupled to said second doped zone.

5. (Once Amended) The device according to claim 4, further comprising a terminal that is coupled to the gate of said second transistor and to the second doped zone.

6. (Once Amended) The device according to claim 4, wherein a drain of said second transistor is coupled to the gate of the first MOS transistor.

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7. (Once Amended) The device according to claim 1, wherein the current limiter comprises a diode, the second doped zone embodying a first terminal of the diode and a third doped zone of a conductivity type opposite that of the conductivity type of the second doped zone embodying a second terminal of the diode.

8. (Once Amended) The device according to claim 7, further comprising a fourth doped zone disposed between the second and third doped zones, said fourth doped zone having the same conductivity type as the conductivity type of either the second or third zones.

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9. (Once Amended) The device according to claim 7, wherein the third doped zone is coupled to the gate of the first MOS transistor.

10. (Once Amended) The device according to claim 8, wherein the diode comprises a gate extending over the fourth doped zone.

11. (Once Amended) The device according to claim 10, wherein said diode gate is coupled to one of the diode terminals.